

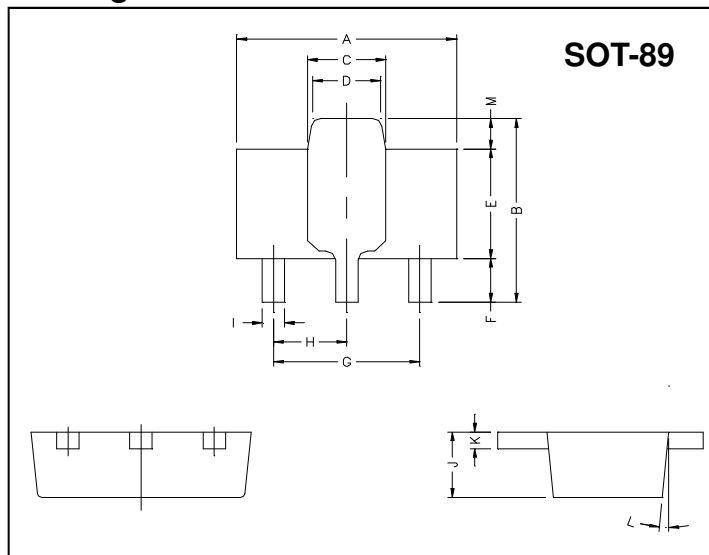
GM3669

NPN EPITAXIAL PLANAR TRANSISTOR

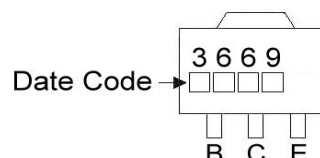
Description

The GM3669 is designed for using in power amplifier applications, power switching application.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at TA = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C
Collector to Base Voltage	V _{CB0}	80	V
Collector to Emitter Voltage	V _{CEO}	80	V
Emitter to Base Voltage	V _{EBO}	5	V
Collect Current(DC)	I _C	2	A
Total Power Dissipation	P _D	1	W

Electrical Characteristics (TA = 25°C)

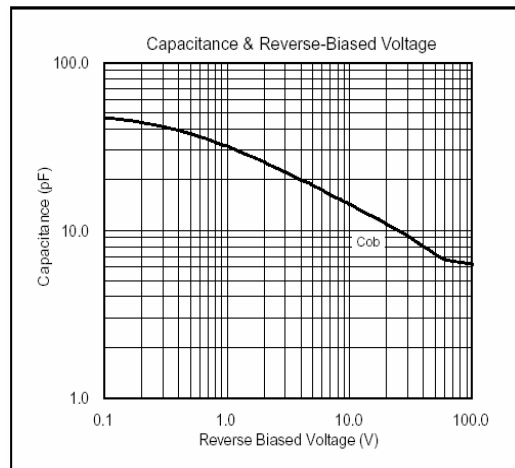
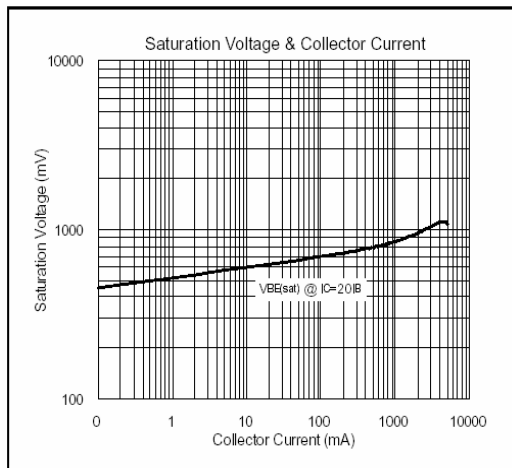
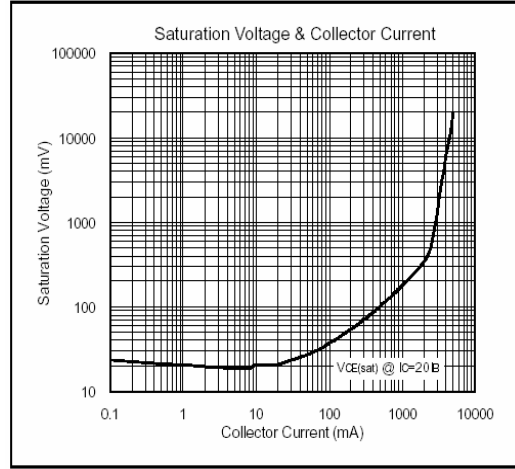
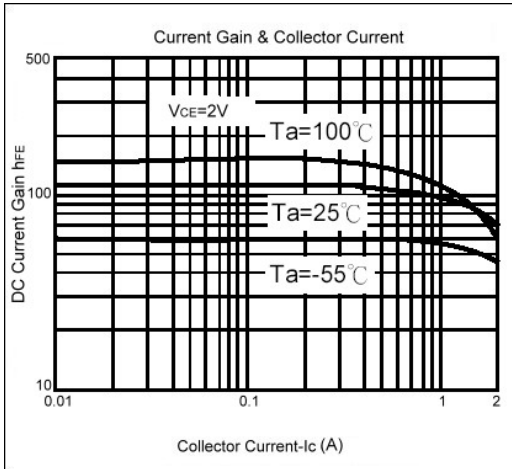
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V _{CB0}	80	-	-	V	I _C =100uA, I _E =0
V _{CEO}	80	-	-	V	I _C =100uA, I _B =0
V _{EBO}	5	-	-	V	I _E =100uA, I _C =0
I _{CB0}	-	-	1	uA	V _{CB} =80V, I _E =0
I _{EBO}	-	-	1	uA	V _{BE} =5V, I _C =0
*V _{CE(sat)}	-	0.15	0.5	V	I _C =1A, I _B =50mA
*V _{BE(sat)}	-	0.9	1.2	V	I _C =1A, I _B =50mA
*h _{FE1}	70	-	240		V _{CE} =2V, I _C =0.5A
*h _{FE2}	40	-	-		V _{CE} =2V, I _C =1.5A
f _T	-	100	-	MHz	V _{CE} =2V, I _C =0.5A
C _{ob}	-	30	-	pF	V _{CB} =10V, f=1MHz
T _{on}	-	0.2	-	uS	V _{CC} =30V, R _L =30Ω, I _C =1A, I _{B1} =-I _{B2} =50mA, Duty Cycle ≤ 1%
T _{stg}	-	1	-		
T _f	-	0.2	-		

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification Of hFE1

Rank	O	Y
Range	70 ~ 140	120 ~ 240

Characteristics Curve



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